

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC7MH165FK

8-Bit Shift Register (P-In, S-Out)

The TC7MH165FK is an advanced high speed CMOS 8-bit parallel/serial-in, serial-out shift register fabricated with silicon gate  $C^2$ MOS technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

It consists of parallel-in or serial-in, serial-out 8-bit shift register with a gated clock input. When the SHIFT/ $\overline{LOAD}$  input is held high, the serial data input is enabled and the eight flip-flops perform serial shifting with each clock pulse.

When the SHIFT/ $\overline{\text{LOAD}}$  input is held low, the parallel data is



Weight: 0.02 g (typ.)

loaded synchronously into the register at positive going transition of the clock pulse.

The CK-INH input should be shifted high only when the CK input is held high.

An Input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and on two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

#### **Features**

- High speed:  $f_{max} = 150 \text{ MHz}$  (typ.) (VCC = 5 V)
- Low power dissipation:  $ICC = 4 \mu A \text{ (max) (Ta} = 25 \text{°C)}$
- High noise immunity: V<sub>NIH</sub> = V<sub>NIL</sub> = 28% V<sub>CC</sub> (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: t<sub>p</sub>LH ≃ t<sub>p</sub>HL
- Wide operating voltage range:  $V_{CC \text{ (opr)}} = 2 \sim 5.5 \text{ V}$
- Pin and function compatible with 74ALS165

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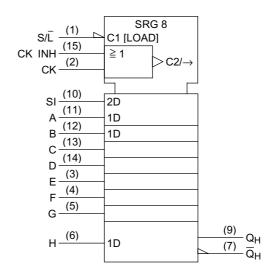
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#### Pin Assignment (top view)

#### $\text{S}/\bar{\text{L}}$ 16 $V_{CC}$ CK CK INH Е D F С G В Н 6 Α $\overline{\mathtt{Q}}_{\mathsf{H}}$ SI 10 GND 8 $Q_H$

#### **IEC Logic Symbol**



#### **Truth Table**

		Inputs		Internal	Outputs	Outputs				
Shift/ LOAD	CK INH	CK	Serial In	Parallel AH	$Q_{A}$	Q <sub>B</sub>	Q <sub>H</sub>	Q <sub>H</sub>		
L	Х	Х	Х	ah	а	b	h	h		
Н	L	_	Н	Х	Н	Q <sub>An</sub>	Q <sub>Gn</sub>	$\overline{\overline{Q}}_{Gn}$		
Н	L	_	L	Х	L	Q <sub>An</sub>	Q <sub>Gn</sub>	$\overline{Q}_Gn$		
Н	<b> </b>	L	Н	Х	Н	Q <sub>An</sub>	Q <sub>Gn</sub>	$\overline{Q}_Gn$		
Н		L	L	Х	L	Q <sub>An</sub>	Q <sub>Gn</sub>	$\overline{Q}_Gn$		
Н	Х	Н	Х	Х	No change					
Н	Н	Х	Х	Х	No change					

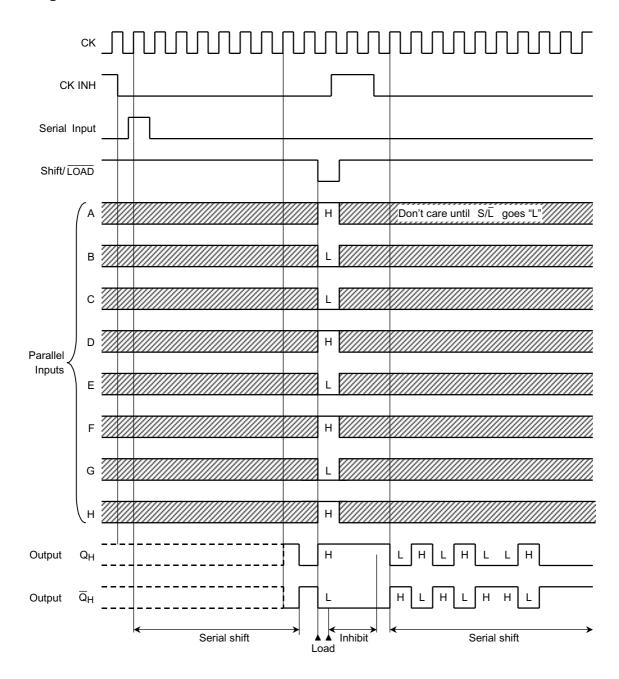
X: Don't care

a .....h: The level of steady state input voltage at inputs A through H respectively

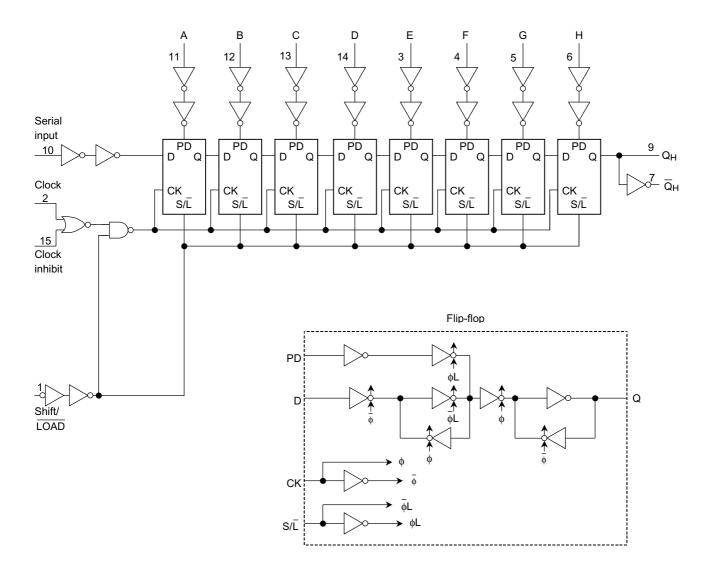
 $Q_{An}$ - $Q_{Gn}$ : The level of  $Q_{A}$ - $Q_{G}$ , respectively, before the most recent positive transition of the CK.



### **Timing Chart**



### **System Diagram**





### **Maximum Ratings**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V
DC input voltage	V <sub>IN</sub>	-0.5~7.0	V
DC output voltage	V <sub>OUT</sub>	-0.5~V <sub>CC</sub> + 0.5	٧
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	I <sub>OK</sub>	±20	mA
DC output current	lout	±25	mA
DC V <sub>CC</sub> /ground current	Icc	±50	mA
Power dissipation	PD	180	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

## **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	2.0~5.5	V
Input voltage	V <sub>IN</sub>	0~5.5	V
Output voltage	V <sub>OUT</sub>	0~V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	$0\sim100 \text{ (V}_{CC} = 3.3 \pm 0.3 \text{ V)}$ $0\sim20 \text{ (V}_{CC} = 5 \pm 0.5 \text{ V)}$	ns/V

#### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics		Symbol	bol Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
Characte	Gridiation				V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Offic
			_		2.0	1.50	_	_	1.50	_	V
	High level	V <sub>IH</sub>			3.0~5.5	$\begin{array}{c} V_{CC} \\ \times 0.7 \end{array}$	_	_	V <sub>CC</sub> ×0.7	_	
Input voltage					2.0	_	_	0.50	_	0.50	
	Low level	V <sub>IL</sub>		_	3.0~5.5	-	-	$\begin{array}{c} V_{CC} \\ \times  0.3 \end{array}$	_	Max —	
	High level				2.0	1.9	2.0	_	1.9	_	
		V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -50 \mu A$	3.0	2.9	3.0	_	2.9	_	- V
					4.5	4.4	4.5	_	4.4	_	
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48	_	
Output voltage				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80	_	
Output Voltage	Low level	V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	Ι <sub>ΟL</sub> = 50 μΑ	2.0	_	0	0.1	_	0.1	
					3.0	_	0	0.1	_	0.1	
					4.5		0	0.1	_	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0	_	_	0.36	_	0.44	
				$I_{OL} = 8 \text{ mA}$	4.5			0.36	_	0.44	
Input leakage current		I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V or GND		0~5.5	_		±0.1	_	±1.0	μΑ
Quiescent supply current		I <sub>CC</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5			4.0		40.0	μΑ



# Timing Requirements (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition			25°C	Ta = -40~85°C	Unit	
Characteristics	Symbol	rest Condition	V <sub>CC</sub> (V)	Тур.	Limit	Limit	Offic	
Minimum pulse width	t <sub>w (L)</sub>		$3.3\pm0.3$	_	6.0	7.0	ns	
(CK, CK INH)	t <sub>w (H)</sub>	<del>_</del>	$5.0\pm0.5$	_	4.0	4.0	119	
Minimum pulse width	4		$3.3\pm0.3$	_	7.5	9.0	no	
( S/L )	t <sub>W (L)</sub>	_	$5.0\pm0.5$	_	5.0	6.0	ns	
Minimum set-up time	4		$3.3\pm0.3$	_	7.5	8.5	ns	
(A~H- S/L )	t <sub>s</sub>	_	$5.0\pm0.5$	_	5.0	5.0		
Minimum set-up time	4		$3.3\pm0.3$	_	5.0	6.0	ns	
(SI-CK, CK INH)	ts	_	$5.0\pm0.5$	_	4.0	4.0	115	
Minimum set-up time	4		$3.3\pm0.3$	_	5.0	6.0	20	
(S/L -CK, CK INH)	t <sub>s</sub>	_	$5.0\pm0.5$	_	4.0	4.0	ns	
Minimum hold time	4.		$3.3 \pm 0.3$	_	0.5	0.5	20	
(A~H- S/L )	t <sub>h</sub>	<del>_</del>	$5.0\pm0.5$	_	1.0	1.0	ns	
Minimum hold time	4.		$3.3 \pm 0.3$	_	0	0	20	
(SI-CK, CK INH)	t <sub>h</sub>	<del>_</del>	$5.0\pm0.5$	_	0.5	0.5	ns	
Minimum hold time	4.		$3.3\pm0.3$	_	0	0	ns	
(S/L -CK, CK INH)	t <sub>h</sub>	_	$5.0\pm0.5$	_	0.5	0.5	115	
Minimum removal time			$3.3 \pm 0.3$	_	5.0	5.0		
(CK INH-CK)	t <sub>rem</sub>	_	$5.0 \pm 0.5$		3.5	3.5	ns	
(CK-CK INH)			3.0 ± 0.5		ა.ა	3.0		



### AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

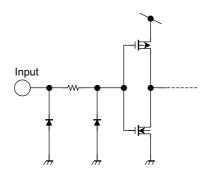
Characteristics	Symbol Test Condition				Ta = 25°C			Ta = -4	0~85°C	Unit
Characteristics	Symbol	rest Condition	V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Uniit
			3.3 ± 0.3	15	_	9.9	15.4	1.0	18.0	- - ns
Propagation delay time	t <sub>pLH</sub>		3.3 ± 0.3	50	_	12.4	18.9	1.0	21.5	
(CK, CK INH-Q <sub>H</sub> , $\overline{Q}_H$ )	t <sub>pHL</sub>	<u>—</u>	5.0 ± 0.5	15		6.6	9.9	1.0	11.5	
			3.0 ± 0.5	50		8.1	11.9	1.0	13.5	
			$3.3 \pm 0.3$	15		9.9	15.8	1.0	18.5	- ns
Propagation delay time	t <sub>pLH</sub> t <sub>pHL</sub>		3.3 ± 0.3	50		12.4	19.3	1.0	22.0	
$(S/L-Q_H, \overline{Q}_H)$		_	5.0 ± 0.5	15		6.7	9.9	1.0	11.5	
			3.0 ± 0.5	50		8.2	11.9	1.0	13.5	
	t <sub>pLH</sub> t <sub>pHL</sub>	_	$3.3 \pm 0.3$	15		9.2	14.1	1.0	16.5	ns
Propagation delay time			0.0 ± 0.0	50		11.7	17.6	1.0	20.0	
$(H-Q_H, \overline{Q}_H)$			5.0 ± 0.5	15		5.9	9.0	1.0	10.5	
				50		7.4	11.0	1.0	12.5	
		_	$3.3 \pm 0.3$	15	65	85		55		
Maximum clock frequency	f <sub>max</sub>		3.3 ± 0.3	50	60	105		50		- MHz
Maximum clock frequency			5.0 ± 0.5	15	110	150	_	90	_	
				50	95	130		85		
Input capacitance	C <sub>IN</sub>	-				4	10	_	10	pF
Power dissipation capacitance	C <sub>PD</sub>			(Note)		50	_	_		pF

Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

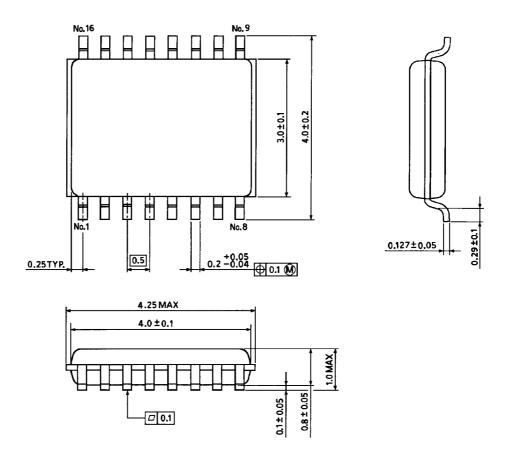
Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

### **Input Equivalent Circuit**



### **Package Dimensions**



Weight: 0.02 g (typ.)